

| | |
|---------------------|-------|
| V_{DSS} | 1200V |
| $R_{DS(on)}$ (Typ.) | 62mΩ |
| I_D^{*1} | 26A |
| P_D | 115W |

● Features

- 1) Low on-resistance
- 2) Fast switching speed
- 3) Fast reverse recovery
- 4) Easy to parallel
- 5) Simple to drive
- 6) Pb-free lead plating ; RoHS compliant

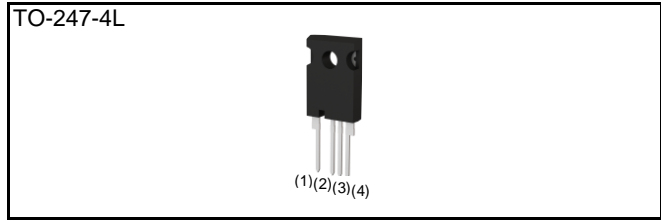
● Application

- Solar inverters
- DC/DC converters
- Switch mode power supplies
- Induction heating
- Motor drives

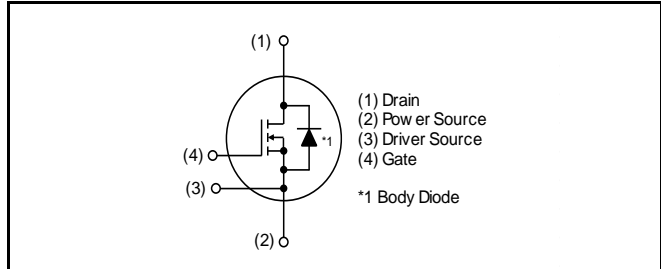
● Absolute maximum ratings ($T_c = 25^\circ\text{C}$)

| Parameter | Symbol | Value | Unit |
|--|------------------------|--------------------|------------------|
| Drain - source voltage | V_{DSS} | 1200 | V |
| Continuous drain and source current $T_c = 100^\circ\text{C}$ | $V_{GS} = V_{GS_{on}}$ | I_D, I_S^{*1} | 26 |
| | | | 18 |
| Pulsed drain current | $V_{GS} = V_{GS_{on}}$ | $I_{D,pulse}^{*2}$ | 52 |
| Body diode pulsed forward current | $V_{GS} = 0\text{ V}$ | $I_{S,pulse}^{*3}$ | 26 |
| Body diode surge forward current | $V_{GS} = 0\text{ V}$ | $I_{S,pulse}^{*4}$ | 52 |
| Gate - source voltage (DC) | V_{GSS_DC} | -4 to +21 | V |
| Gate - source surge voltage ($t_{surge} < 300\text{ns}$) | $V_{GSS_surge}^{*5}$ | -4 to +23 | V |
| Recommended turn-on gate - source drive voltage | $V_{GS_{on}}^{*6}$ | +15 to +18 | V |
| Recommended turn-off gate - source drive voltage | $V_{GS_{off}}$ | 0 | V |
| Virtual junction temperature | T_{vj} | 175 | $^\circ\text{C}$ |
| Range of storage temperature | T_{stg} | -40 to +175 | $^\circ\text{C}$ |

● Outline



● Inner circuit



Please note Driver Source and Power Source are not exchangeable. Their exchange might lead to malfunction.

● Packaging specifications

| Type | Packing | Tube |
|------|---------------------------|-----------|
| | Reel size (mm) | - |
| | Tape width (mm) | - |
| | Basic ordering unit (pcs) | 30 |
| | Taping code | C15 |
| | Marking | SCT4062KR |

●Electrical characteristics ($T_{vj} = 25^{\circ}\text{C}$ unless otherwise specified)

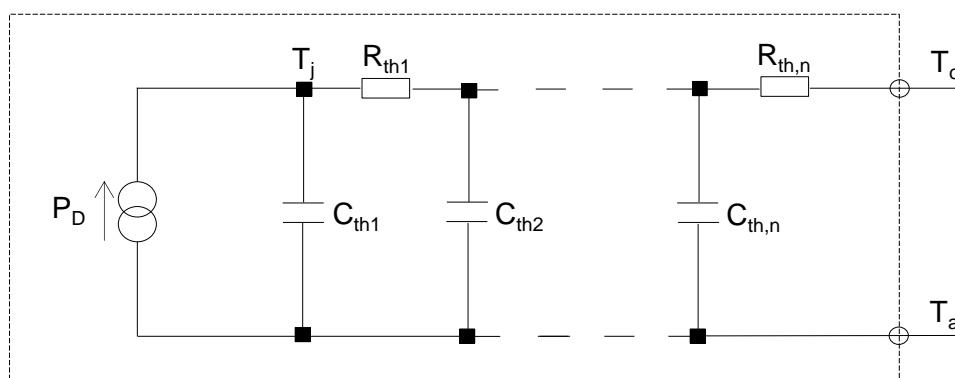
| Parameter | Symbol | Conditions | Values | | | Unit |
|---|-------------------|---|--------|------|------|---------------|
| | | | Min. | Typ. | Max. | |
| Drain - Source breakdown voltage | $V_{(BR)DSS}$ | $V_{GS} = 0\text{ V}, I_D = 5.3\text{mA}$ $T_{vj} = 25^{\circ}\text{C}$ | 1200 | - | - | V |
| Zero Gate voltage Drain current | I_{DSS} | $V_{GS} = 0\text{ V}, V_{DS} = 1200\text{V}$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | - | 1 | 80 | μA |
| Gate - Source leakage current | I_{GSS+} | $V_{GS} = +21\text{ V}, V_{DS} = 0\text{V}$ | - | - | 100 | nA |
| Gate - Source leakage current | I_{GSS-} | $V_{GS} = -4\text{ V}, V_{DS} = 0\text{V}$ | - | - | -100 | nA |
| Gate threshold voltage | $V_{GS(th)}^{*7}$ | $V_{DS} = 10\text{V}, I_D = 6.45\text{mA}$ | 2.8 | - | 4.8 | V |
| Static Drain - Source on - state resistance | $R_{DS(on)}^{*8}$ | $V_{GS} = 18\text{V}, I_D = 12\text{A}$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | - | 62 | 81 | m Ω |
| Gate input resistance | R_G | $f = 1\text{MHz}, \text{open drain}$ | - | 4 | - | Ω |

●Thermal resistance

| Parameter | Symbol | Values | | | Unit |
|-------------------------------------|-----------------|--------|------|------|------|
| | | Min. | Typ. | Max. | |
| Thermal resistance, junction - case | R_{thJC}^{*9} | - | 0.98 | 1.3 | K/W |

●Typical Transient Thermal Characteristics

| Symbol | Value | Unit | Symbol | Value | Unit |
|-----------|----------------------|------|-----------|----------------------|------|
| R_{th1} | 1.7×10^{-1} | K/W | C_{th1} | 3.6×10^{-4} | Ws/K |
| R_{th2} | 4.1×10^{-1} | | C_{th2} | 1.5×10^{-3} | |
| R_{th3} | 4.0×10^{-1} | | C_{th3} | 6.5×10^{-3} | |



●Electrical characteristics ($T_{vj} = 25^{\circ}\text{C}$ unless otherwise specified)

| Parameter | Symbol | Conditions | Values | | | Unit |
|--|-------------------|---|--------|------|------|---------------|
| | | | Min. | Typ. | Max. | |
| Transconductance | g_{fs}^{*8} | $V_{DS} = 10\text{V}, I_D = 12\text{A}$ | - | 6.5 | - | S |
| Input capacitance | C_{iss} | $V_{GS} = 0\text{V}$ | - | 1498 | - | pF |
| Output capacitance | C_{oss} | $V_{DS} = 800\text{V}$ | - | 45 | - | |
| Reverse transfer capacitance | C_{rss} | $f = 1\text{MHz}$ | - | 3 | - | |
| Effective output capacitance, energy related | $C_{o(er)}$ | $V_{GS} = 0\text{V}$ $V_{DS} = 0\text{V to } 800\text{V}$ | - | 54 | - | pF |
| Total Gate charge | Q_g^{*8} | $V_{DS} = 800\text{V}$ $I_D = 12\text{A}$ | - | 64 | - | nC |
| Gate - Source charge | Q_{gs}^{*8} | $V_{GS} = 18\text{V}$ | - | 14 | - | |
| Gate - Drain charge | Q_{gd}^{*8} | See Fig. 1-1, 1-2. | - | 17 | - | |
| Turn - on delay time | $t_{d(on)}^{*8}$ | $V_{DS} = 800\text{V}$ $I_D = 12\text{A}$ | - | 4.4 | - | ns |
| Rise time | t_r^{*8} | $V_{GS} = +18\text{V} / 0\text{V}$ | - | 11 | - | |
| Turn - off delay time | $t_{d(off)}^{*8}$ | $R_G = 0\Omega, L = 250\mu\text{H}$ E_{on} includes diode reverse recovery | - | 22 | - | |
| Fall time | t_f^{*8} | $L_{\sigma} = 50\text{nH}, C_{\sigma} = 10\text{pF}$ | - | 10 | - | |
| Turn - on switching loss | E_{on}^{*8} | See Fig. 2-1, 2-2, 2-3. | - | 132 | - | μJ |
| Turn - off switching loss | E_{off}^{*8} | | - | 6 | - | |

●Body diode electrical characteristics (Source-Drain) ($T_{vj} = 25^{\circ}\text{C}$ unless otherwise specified)

| Parameter | Symbol | Conditions | Values | | | Unit |
|-------------------------------|----------------|--|--------|------|------|------|
| | | | Min. | Typ. | Max. | |
| Forward voltage | V_{SD}^{*8} | $V_{GS} = 0\text{V}, I_D = 12\text{A}$ | - | 3.3 | - | V |
| Reverse recovery time | t_{rr}^{*8} | $I_F = 12\text{A}$ $V_R = 800\text{V}$ | - | 8.1 | - | ns |
| Reverse recovery charge | Q_{rr}^{*8} | $di/dt = 3800\text{A}/\mu\text{s}$ | - | 105 | - | nC |
| Peak reverse recovery current | I_{rrm}^{*8} | $L_{\sigma} = 50\text{nH}, C_{\sigma} = 10\text{pF}$ See Fig. 3-1, 3-2. | - | 26 | - | A |

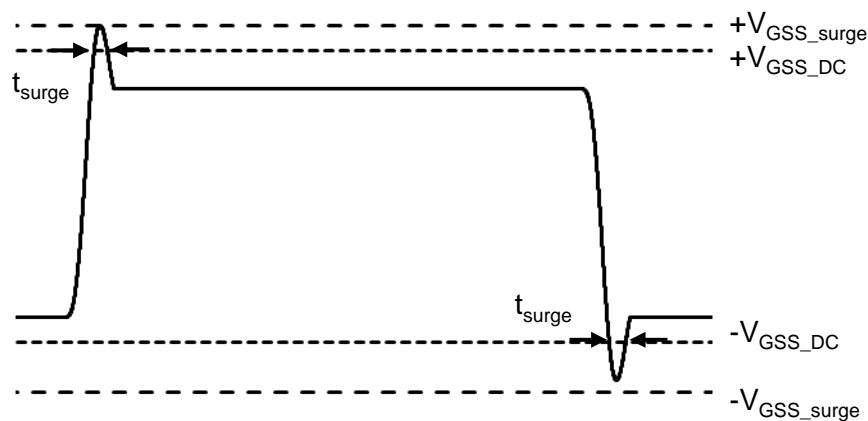
*1 Limited by maximum T_{vj} and for Max. R_{thJC} .

*2 $PW \leq 10\mu\text{s}$, Duty cycle $\leq 1\%$

*3 Only for body-diode, Repetitive pulse, $PW \leq 500\text{ns}$, Duty cycle $\leq 5\%$

*4 When used as a protective function, $PW \leq 10\mu\text{s}$

*5 Example of acceptable V_{GS} waveform



Please note especially when using driver source that V_{GSS_surge} must be in the range of absolute maximum rating.

*6 Please be advised not to use SiC-MOSFETs with V_{GS} below 10V as doing so may cause thermal runaway.

*7 Tested after applying $V_{GS} = 21\text{V}$ for 100ms.

*8 Pulsed

*9 Measured conformable to JESD51-14.

See the application note "rthjc_measurement_and_usage_an-e.pdf". [Link](#)

URL: https://fscdn.rohm.com/en/products/databook/applinote/discrete/common/rthjc_measurement_and_usage_an-e.pdf

●Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

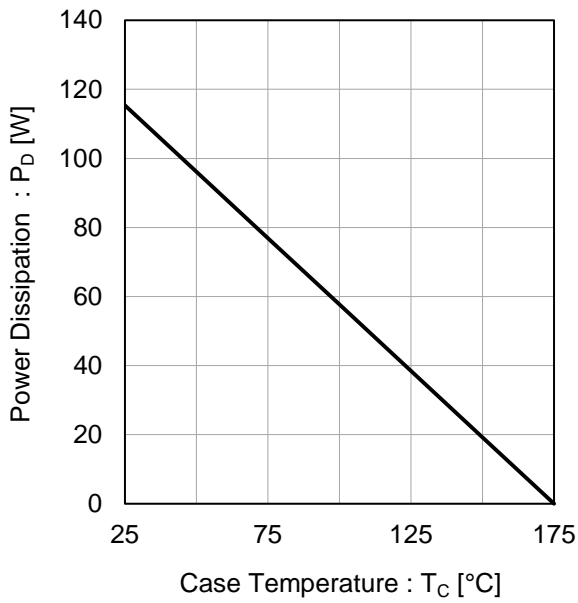


Fig.2 Maximum Safe Operating Area

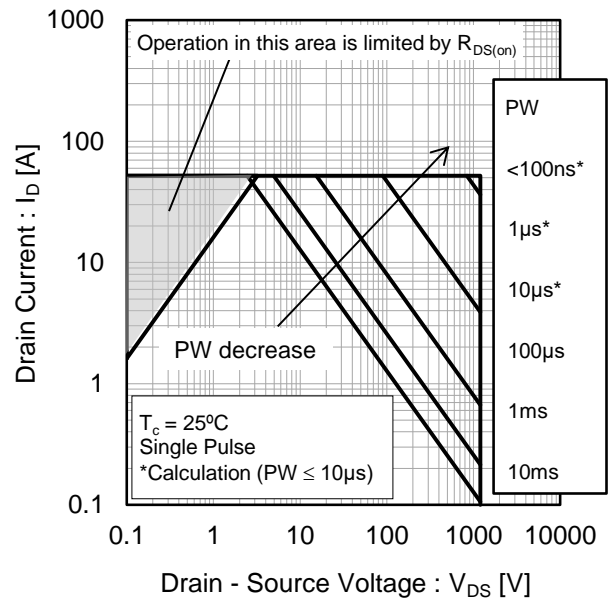
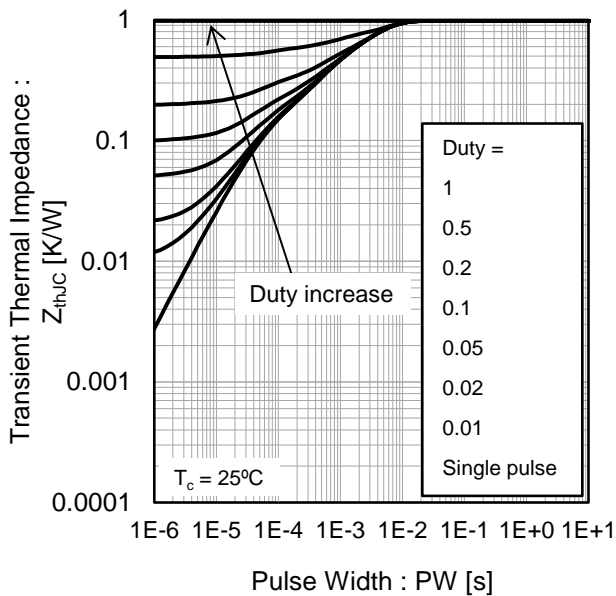


Fig.3 Typical Transient Thermal Impedance vs. Pulse Width



●Electrical characteristic curves

Fig.4 $T_{vj} = 25^{\circ}\text{C}$ Typical Output Characteristics(I)

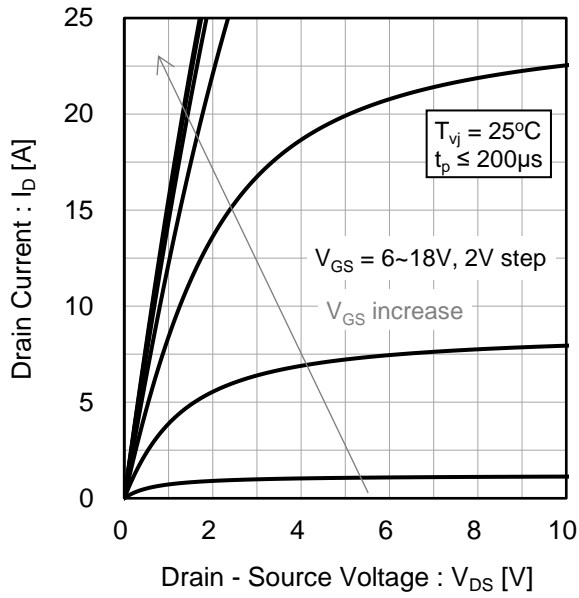


Fig.5 $T_{vj} = 25^{\circ}\text{C}$ Typical Output Characteristics(II)

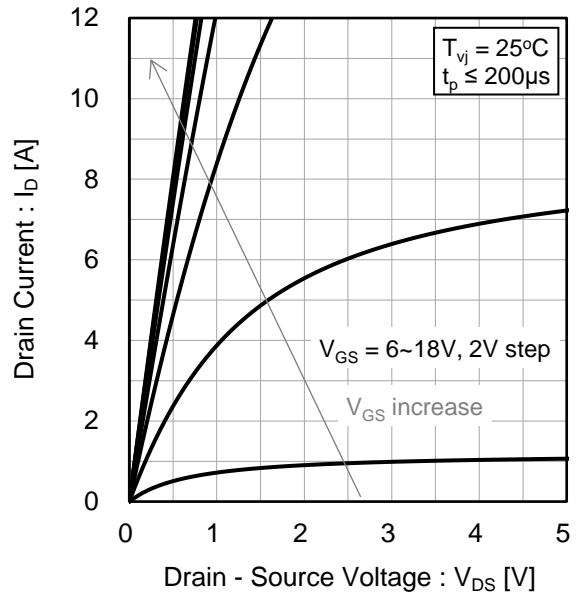
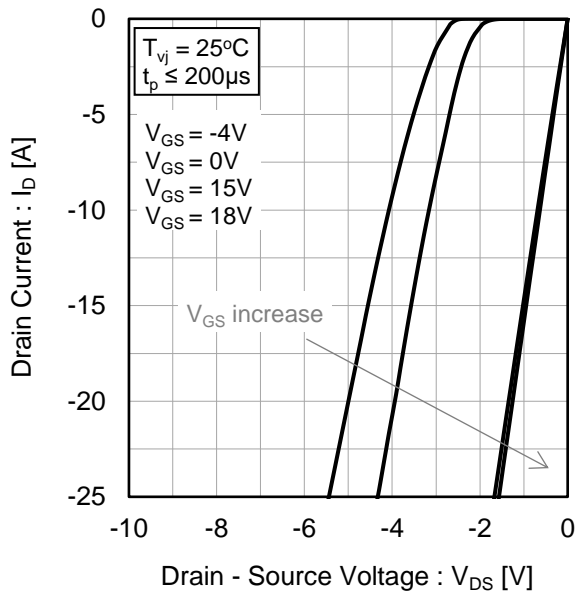


Fig.6 $T_{vj} = 25^{\circ}\text{C}$ 3rd Quadrant Characteristics



●Electrical characteristic curves

Fig.7 $T_{vj} = 150^{\circ}\text{C}$ Typical Output Characteristics(I)

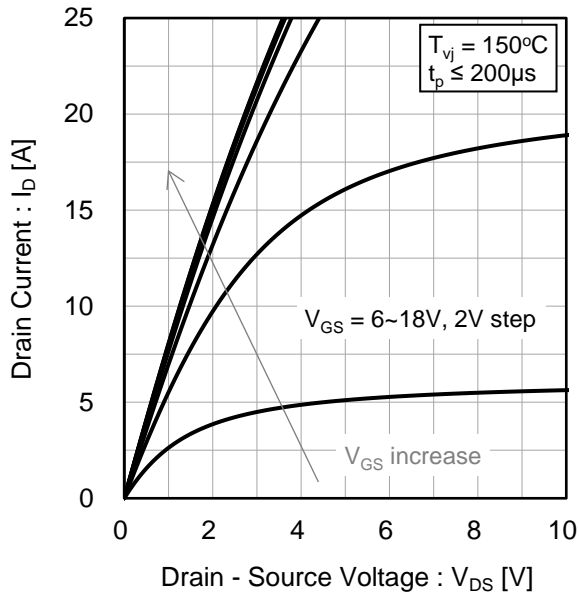


Fig.8 $T_{vj} = 150^{\circ}\text{C}$ Typical Output Characteristics(II)

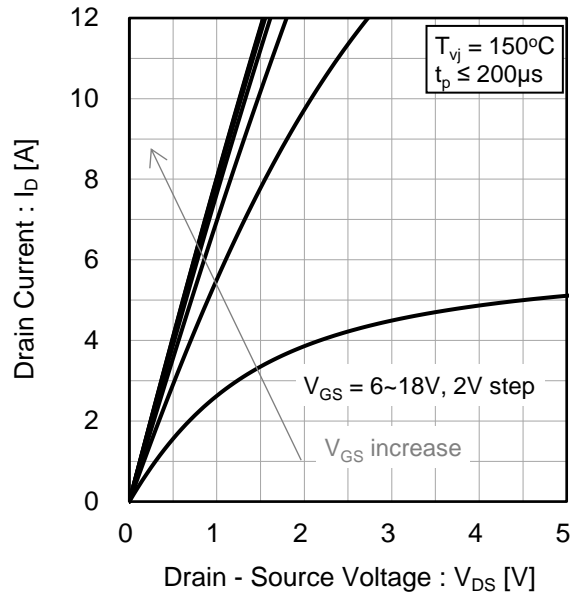


Fig.9 $T_{vj} = 150^{\circ}\text{C}$ 3rd Quadrant Characteristics

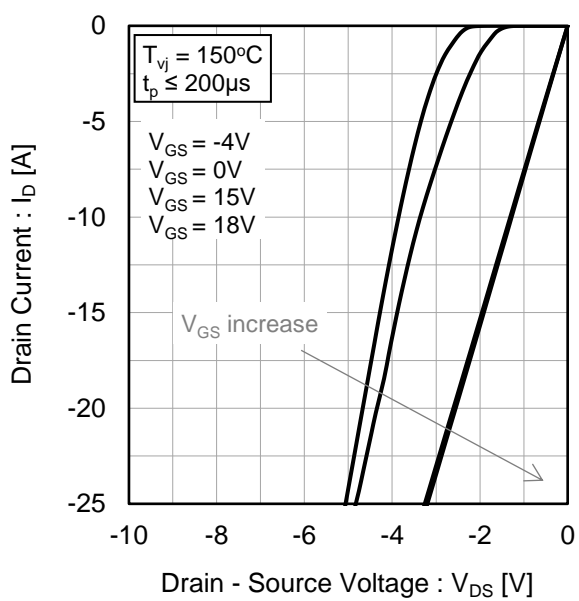
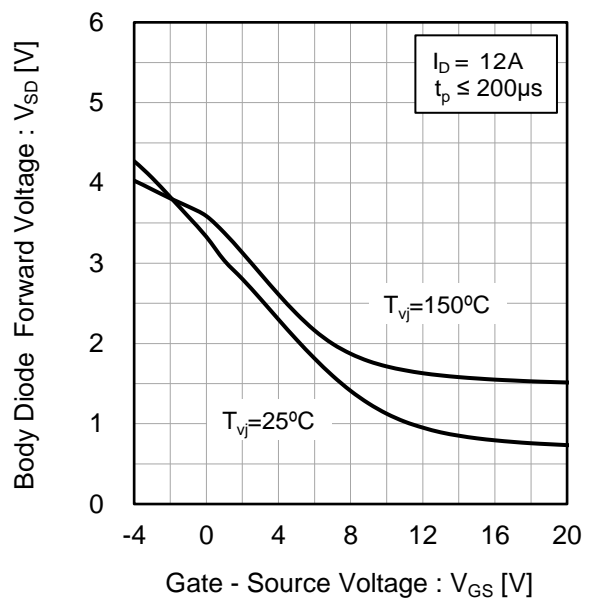


Fig.10 Body Diode Forward Voltage vs. Gate - Source Voltage



●Electrical characteristic curves

Fig.11 Typical Transfer Characteristics (I)

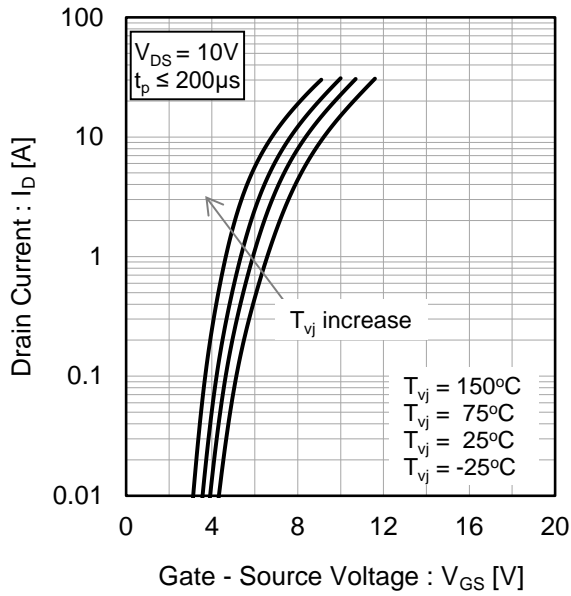


Fig.12 Typical Transfer Characteristics (II)

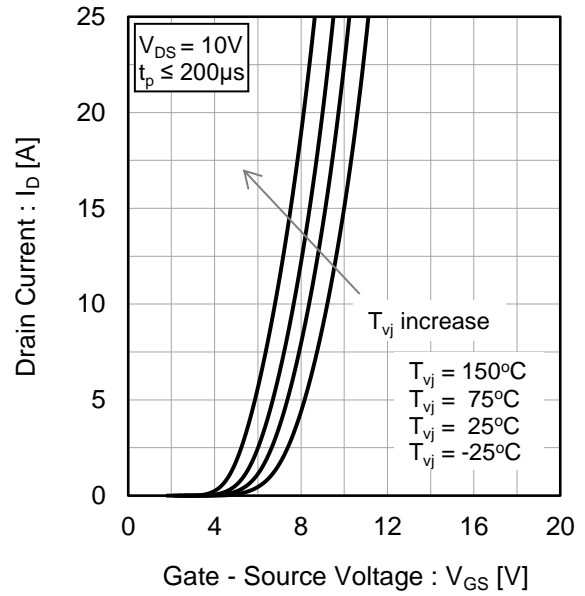


Fig.13 Gate Threshold Voltage vs. Virtual Junction Temperature

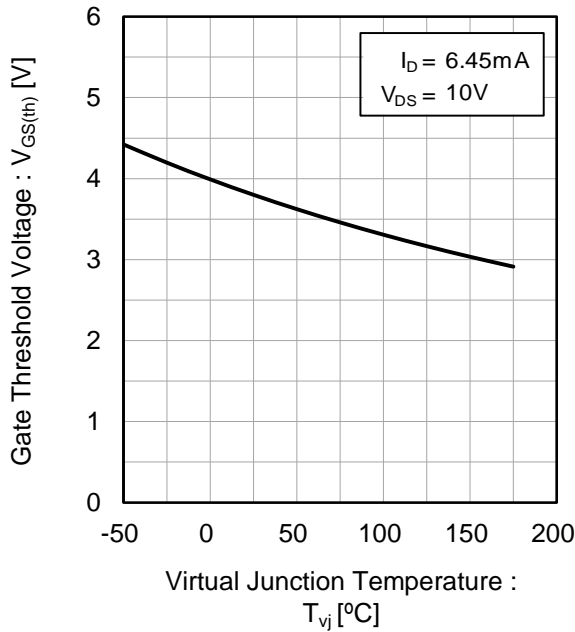
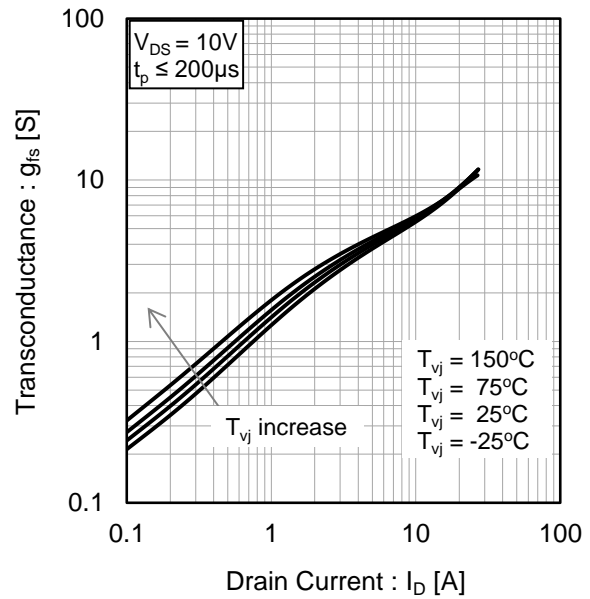


Fig.14 Transconductance vs. Drain Current



●Electrical characteristic curves

Fig.15 Static Drain - Source On - State Resistance vs. Gate - Source Voltage

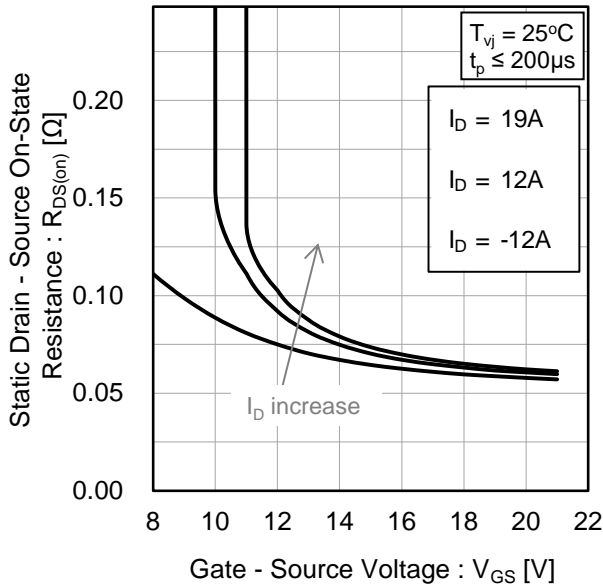


Fig.16 Static Drain - Source On - State Resistance vs. Virtual Junction Temperature

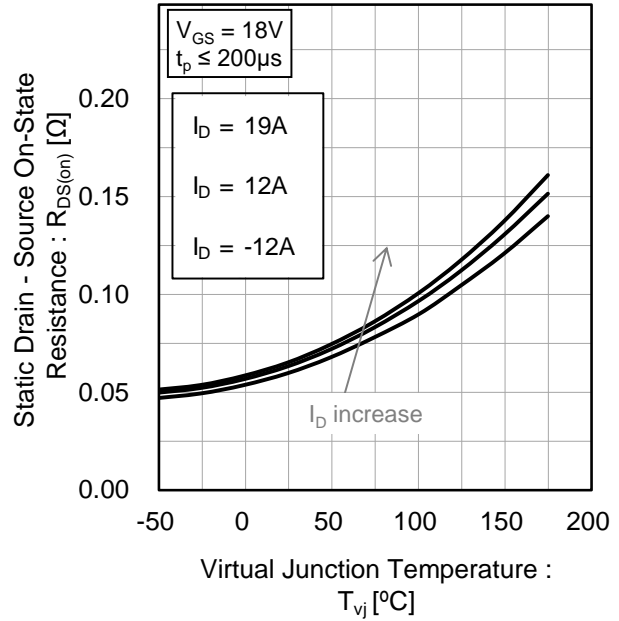


Fig.17 Static Drain - Source On - State Resistance vs. Drain Current

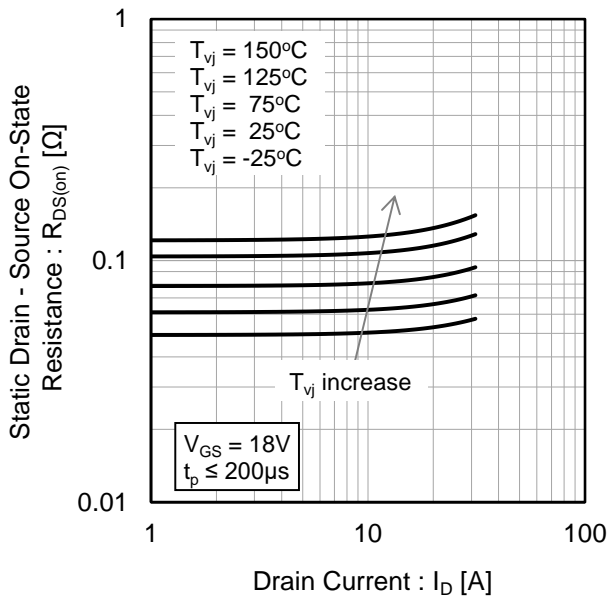
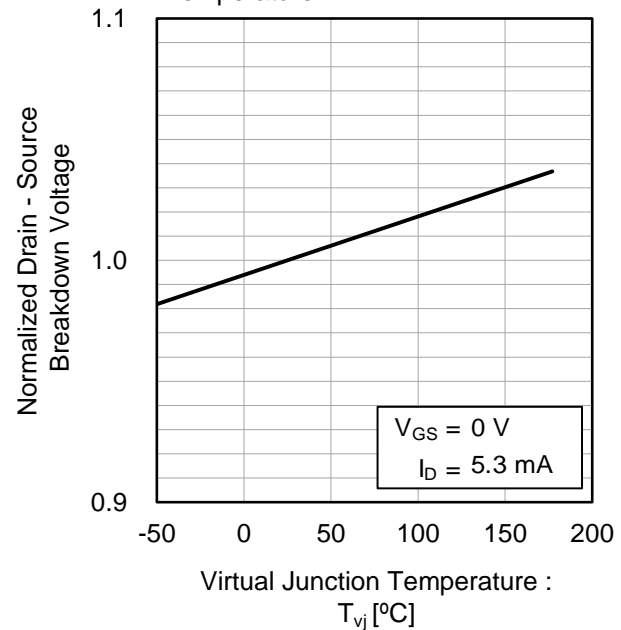


Fig.18 Normalized Drain - Source Breakdown Voltage vs. Virtual Junction Temperature



●Electrical characteristic curves

Fig.19 Typical Capacitance vs. Drain - Source Voltage

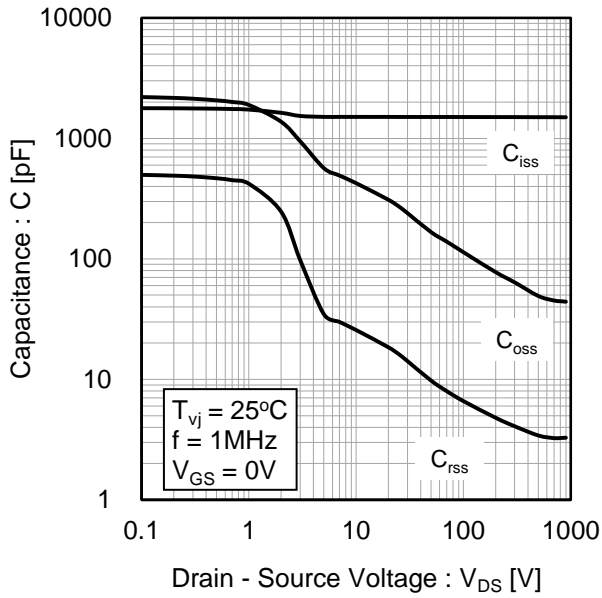


Fig.20 C_{oss} Stored Energy

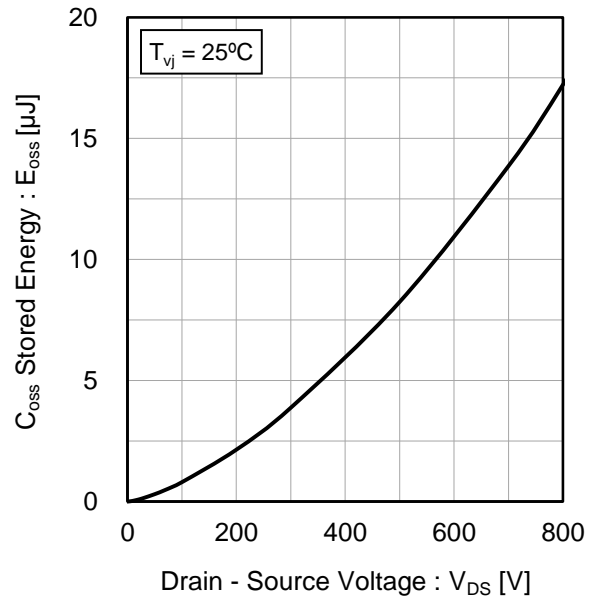
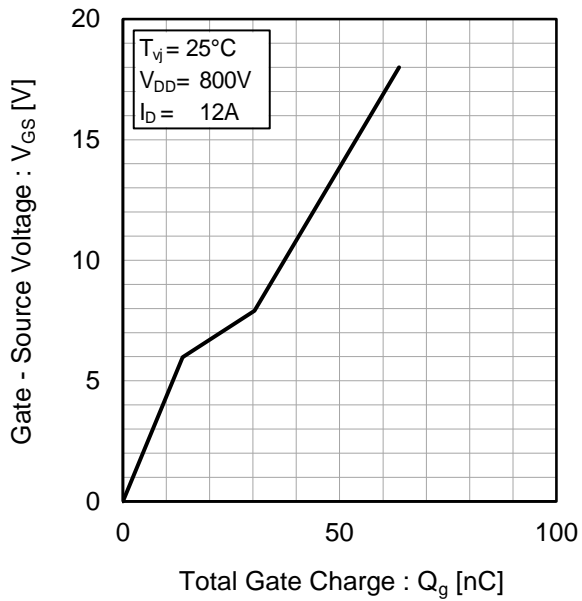


Fig.21 Dynamic Input Characteristics



●Electrical characteristic curves

Fig.22 Typical Switching Time vs. External Gate Resistance

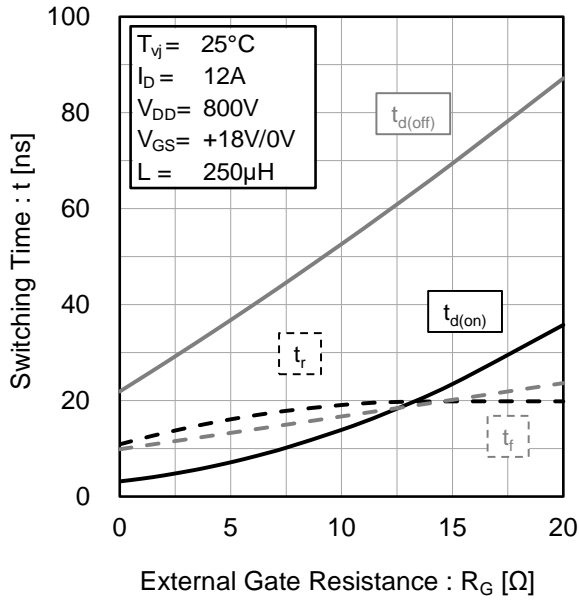


Fig.23 Typical Switching Loss vs. Drain - Source Voltage

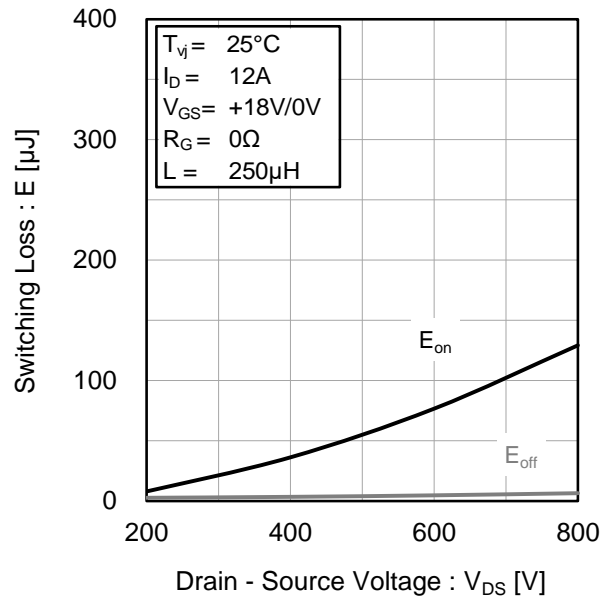


Fig.24 Typical Switching Loss vs. Drain Current

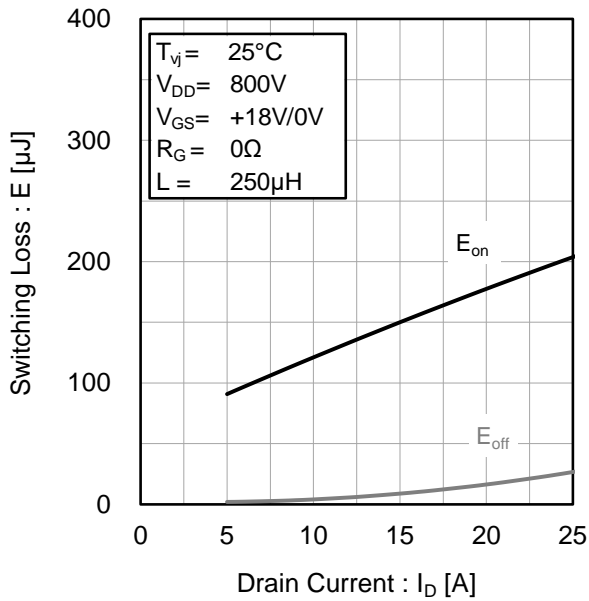
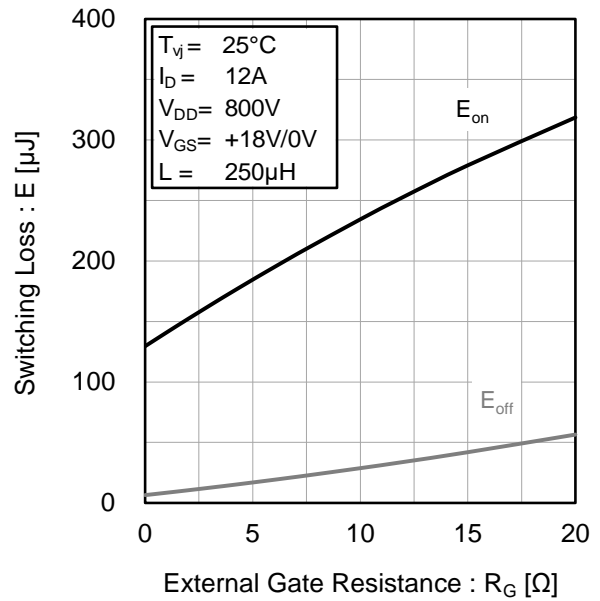


Fig.25 Typical Switching Loss vs. External Gate Resistance



● Measurement circuits and waveforms

Fig.1-1 Gate Charge Measurement Circuit

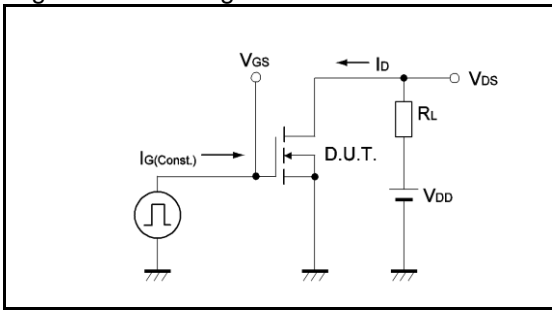


Fig.1-2 Gate Charge Waveform

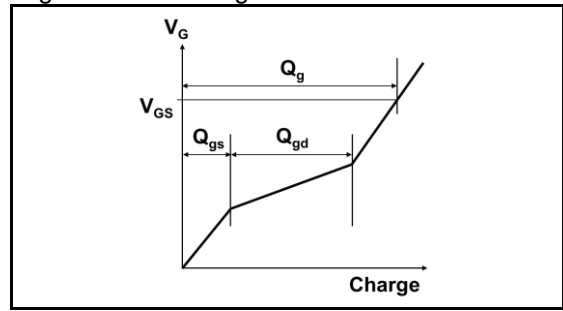


Fig.2-1 Switching Characteristics Measurement Circuit

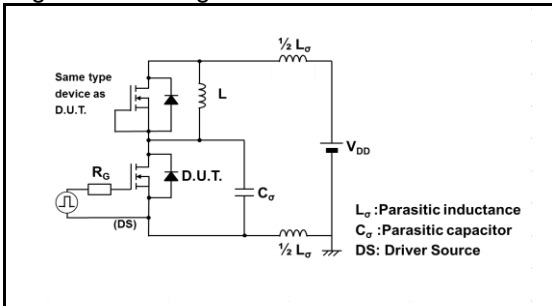


Fig.2-2 Waveforms for Switching Time

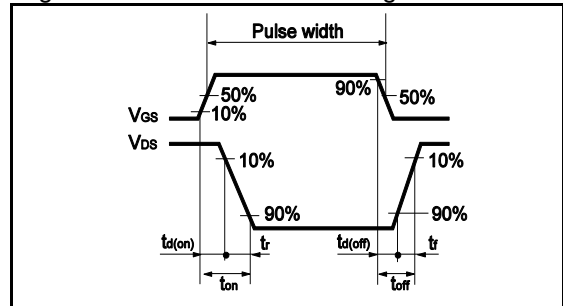


Fig.2-3 Waveforms for Switching Energy Loss

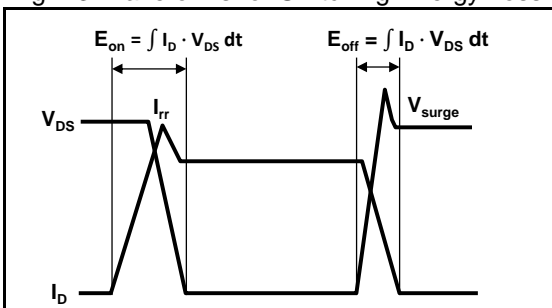


Fig.3-1 Reverse Recovery Time Measurement Circuit

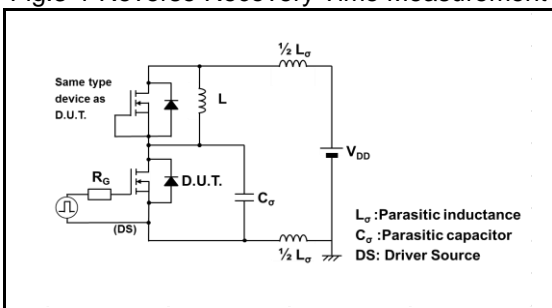
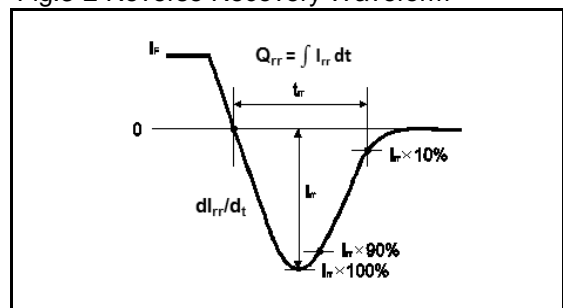
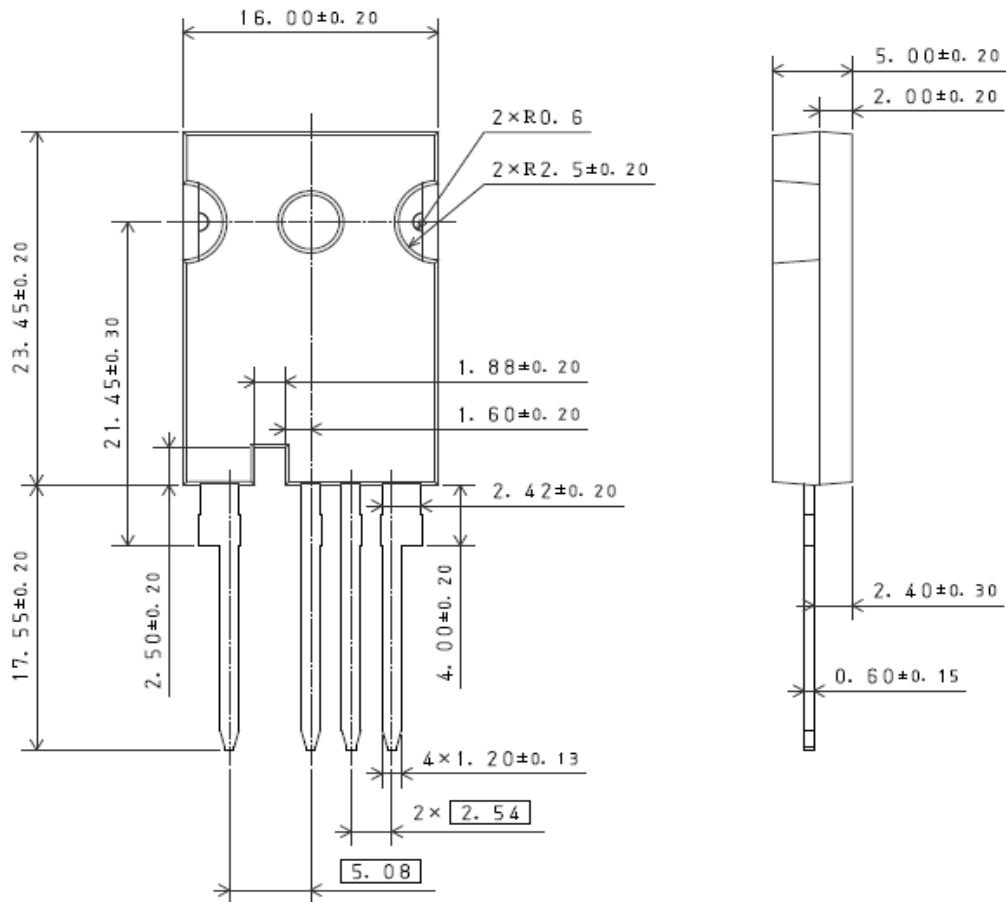


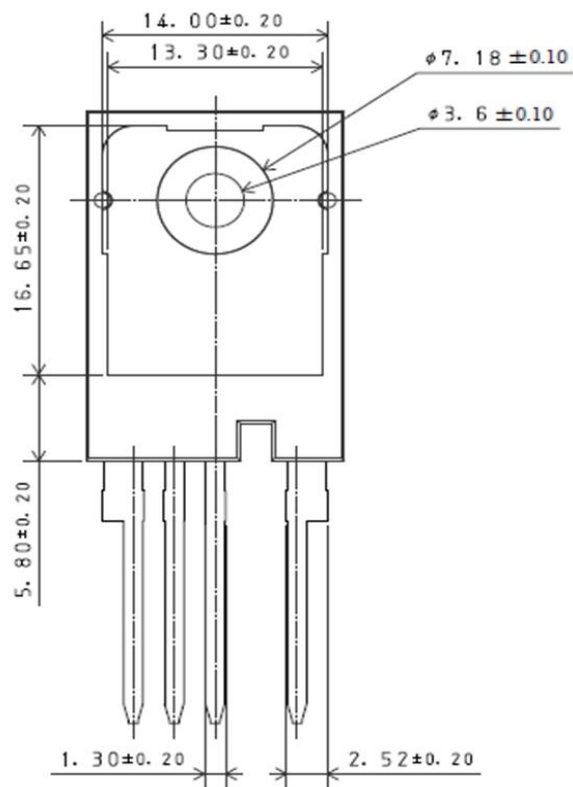
Fig.3-2 Reverse Recovery Waveform



●Package Dimensions

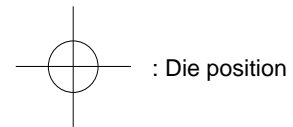
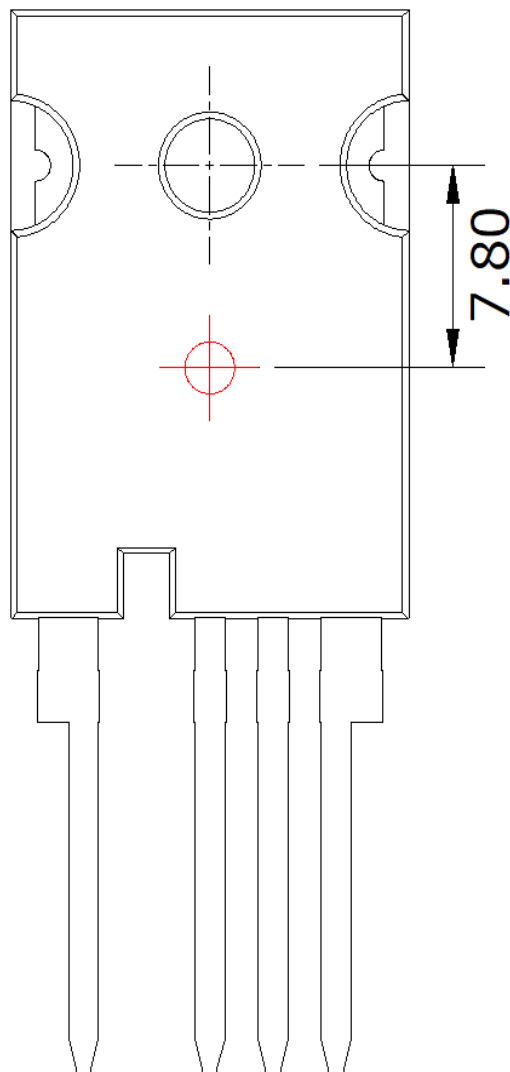


Unit: mm



Unit: mm

●Die Bonding Layout



- Front view of the packaging.
- Dimensions are design values.
- If the heat sink is to be installed, it should be in contact with the die bonding point.

Unit: mm

Notes

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